

Silicon-Based Technology Corp.

Small-Signal Schottky Barrier Diodes

SBT46D Series

SBT46D series are Schottky Barrier Diodes fabricated by a series of proprietary Schottky barrier patents and technologies (SBT[®]) developed by Silicon-Based Technology Corporation, which exhibit high-performance characteristics for modern switching, conversion and protection applications with high speed and low power consumptions. The package types as described in this data sheet are set forth in routine production; other packages are available upon special orders.

■ Features and Advantages:

- Low forward voltage drop (V_F)
- Low reverse leakage current (I_R)
- Very small conduction power loss
- Very small switching power loss
- Very high switching speed
- Very high reliability

■ Electrical Characteristics : (@ $T_A=25^{\circ}\text{C}$ unless otherwise specified)

Characteristic	Symbol	Min.	Typ.	Max.	Unit	Test Conditions
Reverse Breakdown Voltage (Note 2)	$V_{(BR)R}$	100		-	V	$I_R=100\mu\text{A}$
Forward Voltage (Note 2)	V_F	-	-	0.2 0.4 0.8	V	$I_F=0.1\text{mA}$ $I_F=10\text{mA}$ $I_F=250\text{mA}$
Peak Reverse Current (Note 2)	I_R	-	-	0.3 5.0 0.5 7.5 1.0 15 2.0 20	μA	$V_R=1.5\text{V}$ $V_R=1.5\text{V}, T_j=60^{\circ}\text{C}$ $V_R=10\text{V}$ $V_R=10\text{V}, T_j=60^{\circ}\text{C}$ $V_R=50\text{V}$ $V_R=50\text{V}, T_j=60^{\circ}\text{C}$ $V_R=75\text{V}$ $V_R=75\text{V}, T_j=60^{\circ}\text{C}$
Total Capacitance	C_T	-	10 6.0	-	pF	$V_R=0\text{V}, f=1.0\text{MHz}$ $V_R=1.0\text{V}, f=1.0\text{MHz}$



Silicon-Based Technology Corporation

1F, No. 23, R&D Rd. I, Hsinchu Science Park, Taiwan, R.O.C

Tel : 886-3-5777897

Fax : 886-3-5779832

**■ Maximum Ratings : (@T_A=25°C unless otherwise specified)**

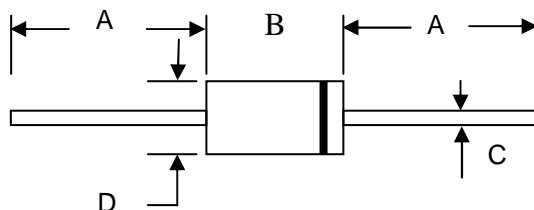
Characteristic	Symbol	Value	Unit
Peak Repetitive Reverse Voltage	V _{RRM}		
Working Peak Reverse Voltage	V _{RWM}	100	V
DC Blocking Voltage	V _R		
Average Rectified Forward Current	I _O	75	mA
Forward Continuous Current (Note 1)	I _F	150	mA
Repetitive Peak Forward Current (Note 1) @t<1.0s, Duty Cycle<50%	I _{FRM}	350	mA
Forward Surge Forward Current (Note 1) @t=10ms	I _{FSM}	750	mA
Power Dissipation (Note 1)	P _d	200	mW
Thermal Resistance, Junction to Ambient Air (Note 1)	R _{θJA}	500	°C/W
Operating and Storage Temperature Range	T _j , T _{STG}	-55 to +125	°C

- Notes: 1. Valid provided that electrodes are kept at ambient temperature.
2. t<300µs, Duty Cycle<2%.
3. RoHS revision 13.2.2003. Glass and High Temperature Solder Exemptions Applied, see EU Directive Annex Notes 6 and 7.

■ Package Data :

- Case: Molded Plastic Material (UL Flammability Classification 94V-0)
- Terminals: Solderable Plated Terminals (MIL-STD-202, Method 208)
- Lead Free Plating (Matte Tin Finish)
- Polarity: See device configurations below
- Approx. Weight: 0.13 grams
- Package outline and dimensions (see below)

DO-35



DIMENSIONS (MM)				
	A	B	C	D
Min.	25.40	-	-	-
Max.	-	4.00	0.60	2.00

■ Ordering Information (Note 4)

Part Number	Marking Code	Packaging Type	Shipping
			7" Tape & Real
SBT46D	SBT46D	DO-35	3K

Notes: 4. Website at <http://www.sbt.com.tw>

5. Bulk package in a box form is also available upon request.

6. Day code marking is YM, in which Y represents year (For example: 2005 is marked by 5);

M represents month in a year (For example: March is marked by C; November is marked by K).